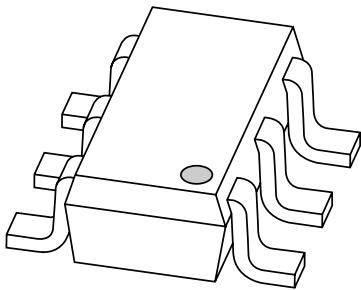


DATA SHEET



PMEM4020PD

PNP transistor/Schottky-diode
module

Product data sheet

2003 Nov 24

PNP transistor/Schottky-diode module

PMEM4020PD

FEATURES

- 600 mW total power dissipation
- High current capability
- Reduces required PCB area
- Reduced pick and place costs
- Small plastic SMD package.

Transistor

- Low collector-emitter saturation voltage.

Diode

- Ultra high-speed switching
- Very low forward voltage
- Guard ring protected.

APPLICATIONS

- DC-to-DC converters
- Inductive load drivers
- General purpose load drivers
- Reverse polarity protection circuits.

DESCRIPTION

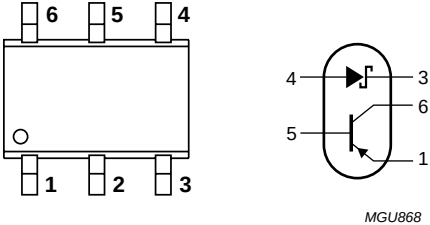
Combination of a PNP transistor with low V_{CEsat} and high current capability and a planar Schottky barrier diode with an integrated guard ring for stress protection in a SOT457 (SC-74) small plastic package.
NPN complement: PMEM4020ND.

ORDERING INFORMATION

TYPE NUMBER	PACKAGE		
	NAME	DESCRIPTION	VERSION
PMEM4020PD	–	plastic surface mounted package; 6 leads	SOT457

PINNING

PIN	DESCRIPTION
1	emitter
2	not connected
3	cathode
4	anode
5	base
6	collector



MGU868

Marking code: B7.

Fig.1 Simplified outline (SOT457) and symbol.

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LIMITING VALUES

In accordance with the Absolute Maximum System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
PNP transistor					
V_{CBO}	collector-base voltage	open emitter	–	–40	V
V_{CEO}	collector-emitter voltage	open base	–	–40	V
V_{EBO}	emitter-base voltage	open collector	–	–5	V
I_C	collector current (DC)	note 1	–	–0.75	A
		note 2	–	–1	A
		note 3	–	–1.3	A
		$T_s \leq 55\text{ °C}$; note 4	–	–2	A
I_{CM}	peak collector current		–	–3	A
I_{BM}	peak base current		–	–1	A
P_{tot}	total power dissipation	$T_{amb} \leq 25\text{ °C}$; note 1	–	295	mW
		$T_{amb} \leq 25\text{ °C}$; note 2	–	400	mW
		$T_{amb} \leq 25\text{ °C}$; note 3	–	500	mW
		$T_s \leq 55\text{ °C}$; note 4	–	1000	mW
T_j	junction temperature		–	150	°C
Schottky barrier diode					
V_R	continuous reverse voltage		–	20	V
I_F	continuous forward current		–	1	A
I_{FSM}	non-repetitive peak forward current	$t = 8.3\text{ ms}$ half sinewave; JEDEC method	–	5	A
P_{tot}	total power dissipation	$T_{amb} \leq 25\text{ °C}$; note 1	–	295	mW
		$T_{amb} \leq 25\text{ °C}$; note 2	–	400	mW
		$T_{amb} \leq 25\text{ °C}$; note 3	–	500	mW
		$T_s \leq 55\text{ °C}$; note 4	–	1000	mW
T_j	junction temperature	note 2	–	150	°C
Combined device					
P_{tot}	total power dissipation	$T_{amb} = 25\text{ °C}$; note 2	–	600	mW
T_{stg}	storage temperature		–65	+150	°C
T_{amb}	operating ambient temperature	note 2	–65	+150	°C

Notes

1. Device mounted on a FR4 printed-circuit board; single-sided copper; tinplated; standard footprint for SOT457.
2. Device mounted on a FR4 printed-circuit board; single-sided copper; tinplated; mounting pads for collector and cathode both 1 cm^2 .
3. Mounted on a ceramic printed-circuit board; single-sided copper; tinplated; standard footprint.
4. Solder point of collector or cathode tab.

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THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
Single device				
R _{th(j-s)}	thermal resistance from junction to solder point	in free air; notes 1 and 2	95	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	in free air; notes 1 and 3	250	K/W
		in free air; notes 1 and 4	315	K/W
		in free air; notes 1 and 5	425	K/W
Combined device				
R _{th(j-a)}	thermal resistance from junction to ambient	in free air; notes 1 and 3	208	K/W

Notes

1. For Schottky barrier diodes thermal run-away has to be considered, as in some applications the reverse power losses P_R are a significant part of the total power losses. Nomograms for determination of the reverse power losses P_R and I_F (AV) rating will be available on request.
2. Solder point of collector or cathode tab.
3. Device mounted on a ceramic printed-circuit board; single-sided copper; tinplated; standard footprint.
4. Device mounted on a FR4 printed-circuit board; single-sided copper; tinplated; mounting pad for collector and cathode both 1 cm².
5. Device mounted on a FR4 printed-circuit board, single-sided copper; tinplated; standard footprint for SOT457.

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ELECTRICAL CHARACTERISTICST_{amb} = 25 °C unless otherwise specified.

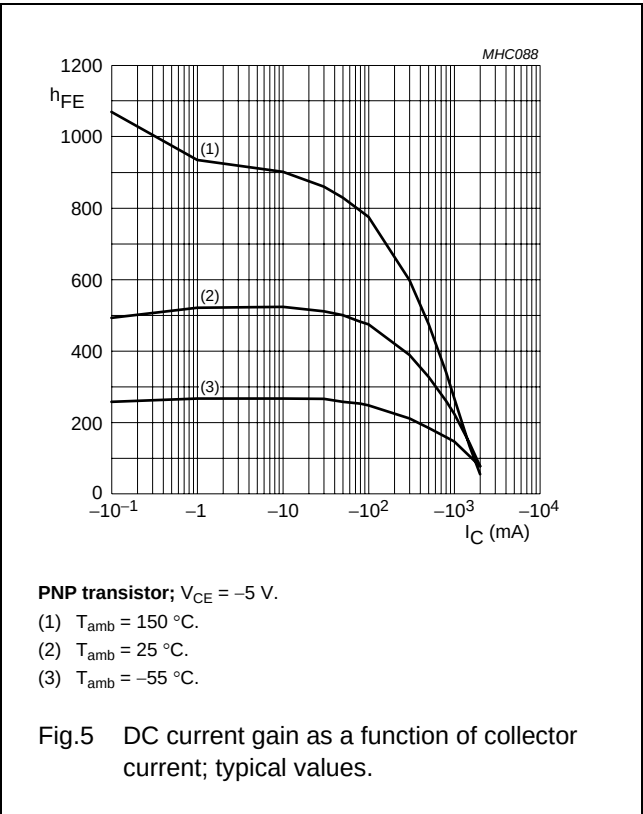
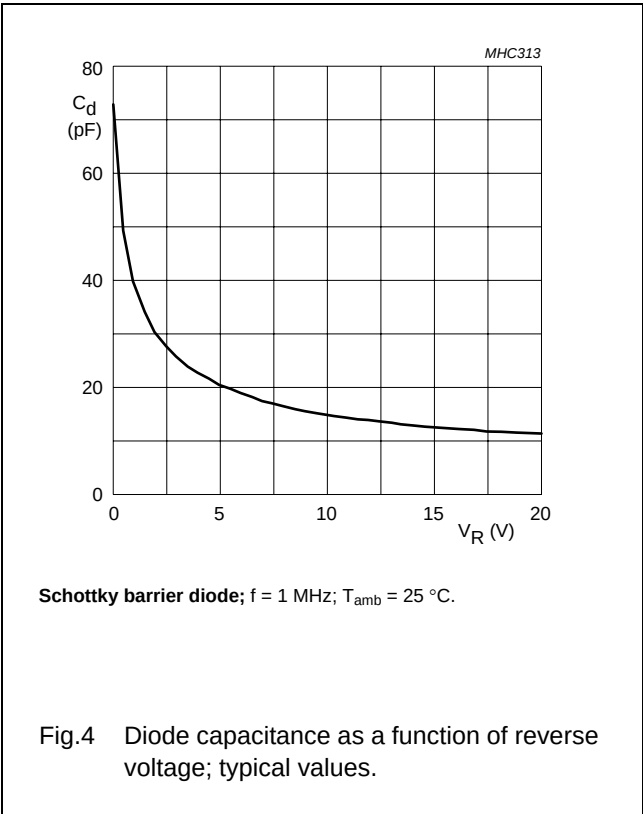
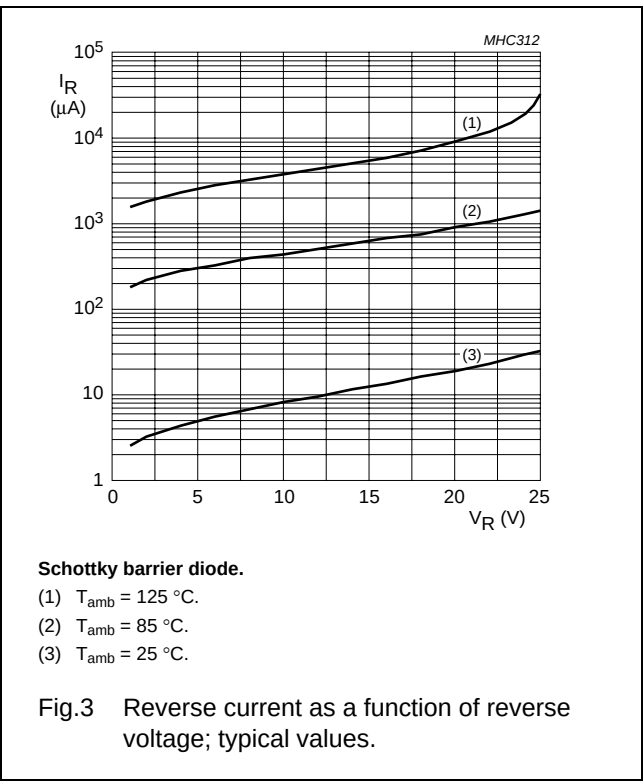
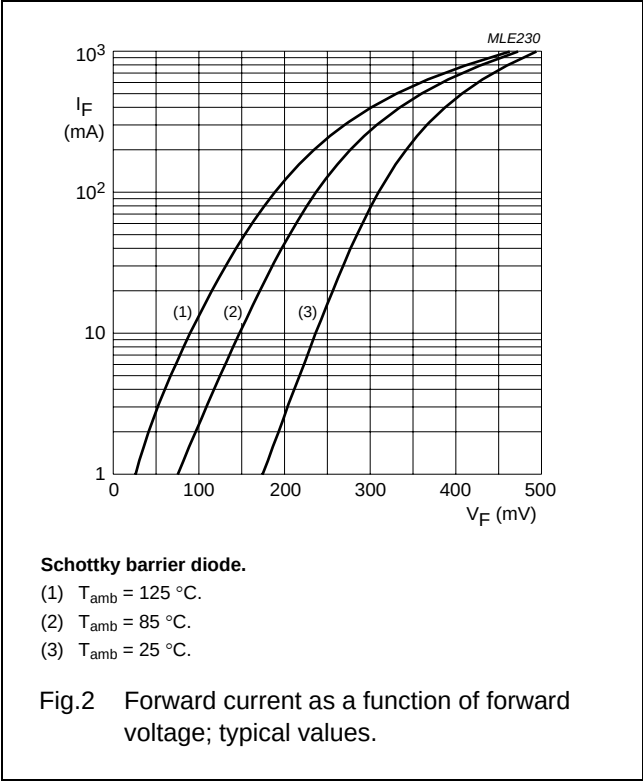
SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
PNP transistor						
I _{CBO}	collector-base cut-off current	V _{CB} = -40 V; I _E = 0	–	–	-100	nA
		V _{CB} = -40 V; I _E = 0; T _{amb} = 150 °C	–	–	-50	μA
I _{CEO}	collector-emitter cut-off current	V _{CE} = -30 V; I _B = 0	–	–	-100	nA
I _{EBO}	emitter-base cut-off current	V _{EB} = -5 V; I _C = 0	–	–	-100	nA
h _{FE}	current gain (DC)	V _{CE} = -5 V; I _C = -1 mA	300	–	–	
		V _{CE} = -5 V; I _C = -100 mA	300	–	800	
		V _{CE} = -5 V; I _C = -500 mA	250	–	–	
		V _{CE} = -5 V; I _C = -1 A	160	–	–	
		V _{CE} = -5 V; I _C = -2 A; note 1	50	–	–	
V _{CEsat}	collector-emitter saturation voltage	I _C = -100 mA; I _B = -1 mA	–	–	-120	mV
		I _C = -500 mA; I _B = -50 mA	–	–	-145	mV
		I _C = -1 A; I _B = -100 mA	–	–	-260	mV
		I _C = -2 A; I _B = -200 mA	–	–	-530	mV
V _{BEsat}	base-emitter saturation voltage	I _C = -1 A; I _B = -50 mA	–	–	-1.1	V
R _{CEsat}	equivalent on-resistance	I _C = -1 A; I _B = -100 mA; note 1	–	180	280	mΩ
V _{BEon}	base-emitter turn-on voltage	V _{CE} = -5 V; I _C = -1 A	–	–	-1	V
f _T	transition frequency	I _C = -50 mA; V _{CE} = -10 V; f = 100 MHz	150	–	–	MHz
Schottky barrier diode						
V _F	continuous forward voltage	see Fig.2; note 1				
		I _F = 10 mA	–	240	270	mV
		I _F = 100 mA	–	300	350	mV
		I _F = 1000 mA	–	480	550	mV
I _R	reverse current	see Fig.3; note 1				
		V _R = 5 V	–	5	10	μA
		V _R = 8 V	–	7	20	μA
		V _R = 15 V	–	10	50	μA
C _d	diode capacitance	V _R = 5 V; f = 1 MHz; see Fig.4	–	19	25	pF

Note1. Pulse test: t_p ≤ 300 μs; δ ≤ 0.02.

PNP transistor/Schottky-diode module

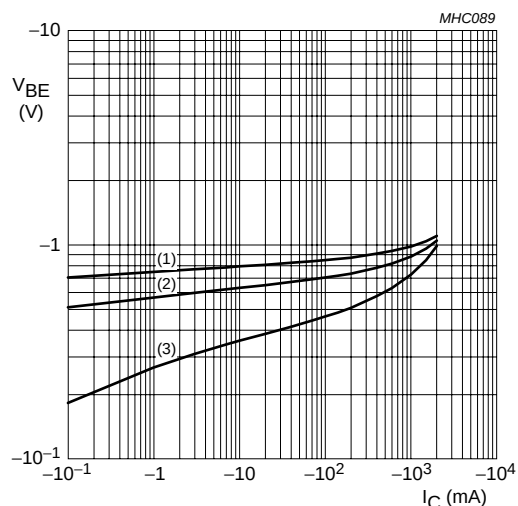
PMEM4020PD

GRAPHICAL DATA



PNP transistor/Schottky-diode module

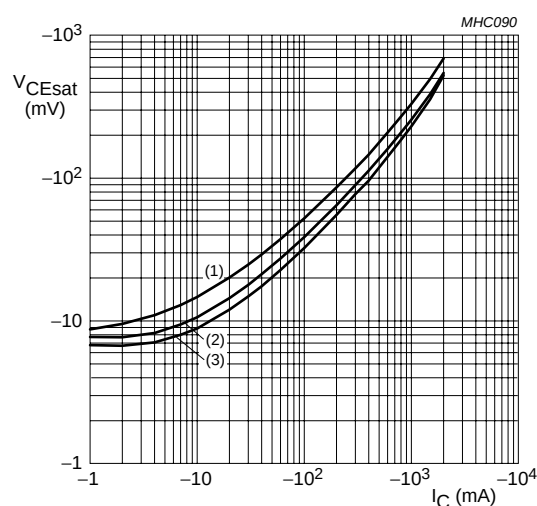
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PNP transistor; $V_{CE} = -5$ V.

- (1) $T_{amb} = -55$ °C.
- (2) $T_{amb} = 25$ °C.
- (3) $T_{amb} = 150$ °C.

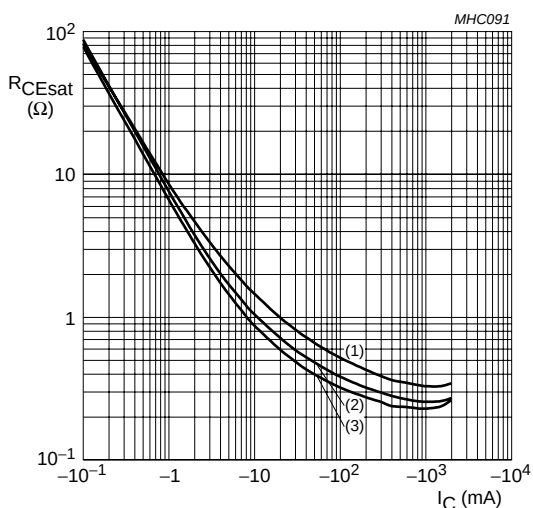
Fig.6 Base-emitter voltage as a function of collector current; typical values.



PNP transistor; $I_C/I_B = 10$.

- (1) $T_{amb} = 150$ °C.
- (2) $T_{amb} = 25$ °C.
- (3) $T_{amb} = -55$ °C.

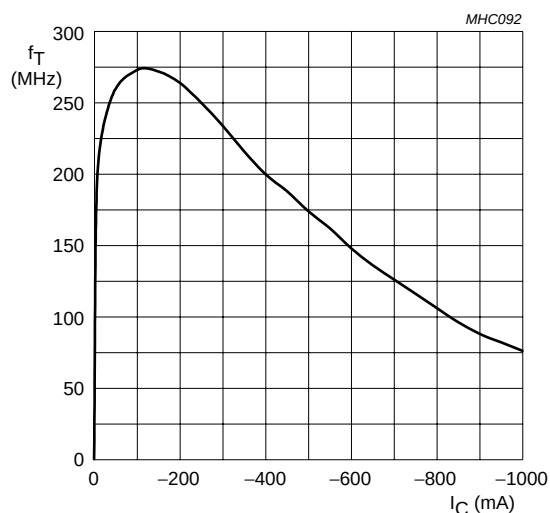
Fig.7 Collector-emitter saturation voltage as a function of collector current; typical values.



PNP transistor; $I_C/I_B = 10$.

- (1) $T_{amb} = 150$ °C.
- (2) $T_{amb} = 25$ °C.
- (3) $T_{amb} = -55$ °C.

Fig.8 Equivalent on-resistance as a function of collector current; typical values.



PNP transistor; $V_{CE} = -10$ V.

Fig.9 Transition frequency as a function of collector current.

PNP transistor/Schottky-diode module

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APPLICATION INFORMATION

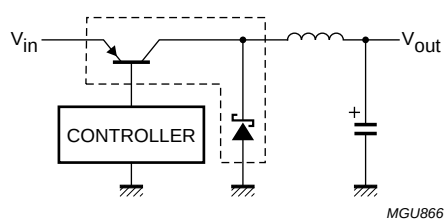


Fig.10 DC-to-DC converter.

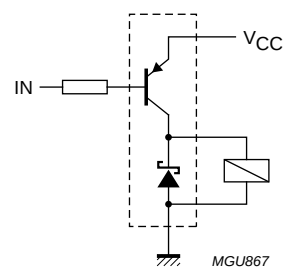


Fig.11 Inductive load driver (relays, motors, buzzers) with free-wheeling diode.

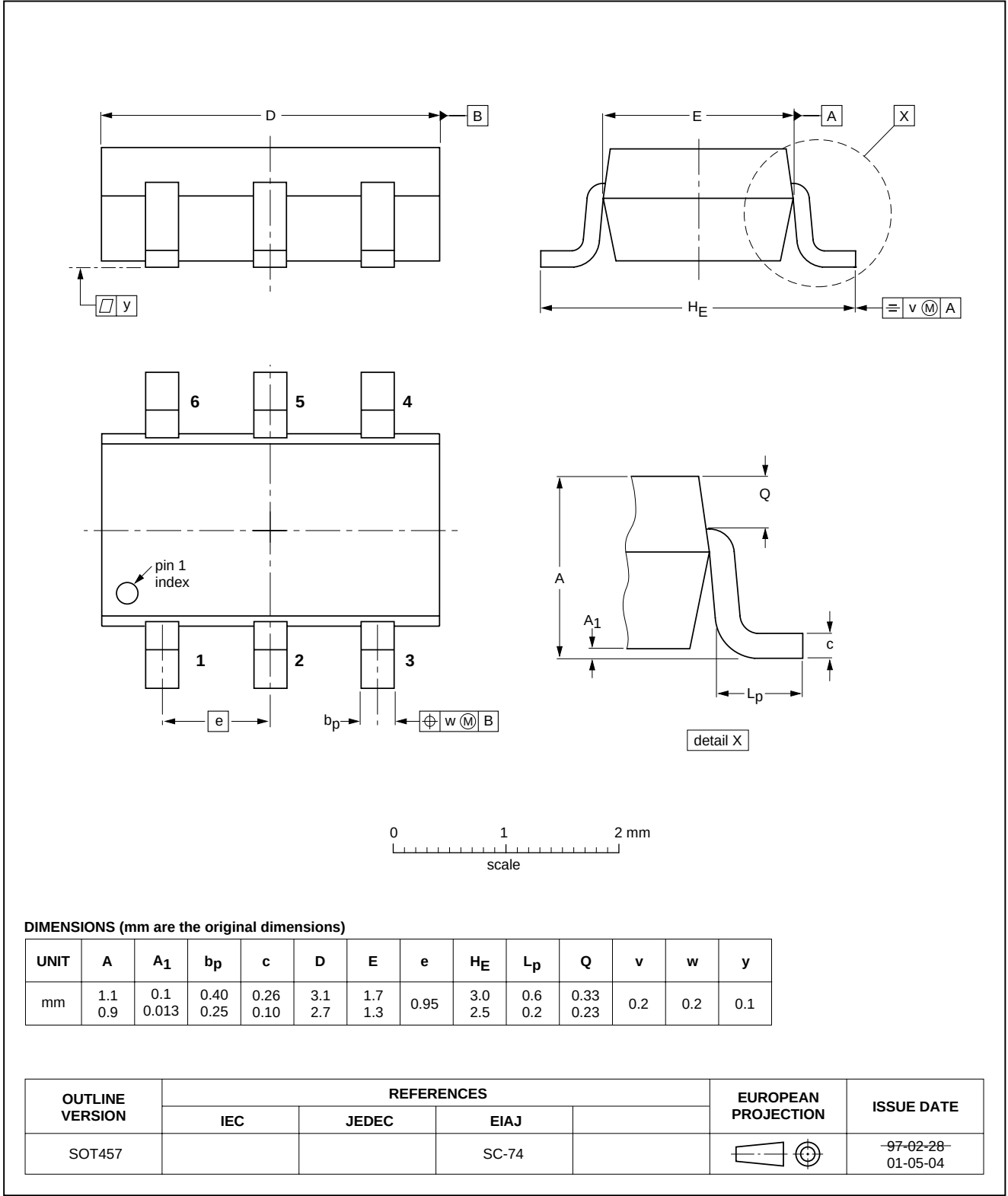
PNP transistor/Schottky-diode module

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PACKAGE OUTLINE

Plastic surface mounted package; 6 leads

SOT457



PNP transistor/Schottky-diode module

PMEM4020PD

DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

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Printed in The Netherlands

R76/01/pp11

Date of release: 2003 Nov 24

Document order number: 9397 750 11907

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